

### BC635/637/639

### **Switching and Amplifier Applications**

• Complement to BC636/638/640



## **NPN Epitaxial Silicon Transistor**

**Absolute Maximum Ratings** T<sub>a</sub>=25°C unless otherwise noted

Symbol	Parameter	Value	Units
V <sub>CER</sub>	Collector-Emitter Voltage at $R_{BE}$ =1 $K\Omega$		
	: BC635	45	V
	: BC637	60	V
	: BC639	100	V
V <sub>CES</sub>	Collector-Emitter Voltage		
	: BC635	45	V
	: BC637	60	V
	: BC639	100	V
V <sub>CEO</sub>	Collector-Emitter Voltage		
	: BC635	45	V
	: BC637	60	V
	: BC639	80	V
V <sub>EBO</sub>	Emitter-Base Voltage	5	V
I <sub>C</sub>	Collector Current	1	А
I <sub>CP</sub>	Peak Collector Current	1.5	А
	Base Current	100	mA
P <sub>C</sub>	Collector Power Dissipation	1	W
T <sub>J</sub>	Junction Temperature	150	°C
T <sub>STG</sub>	Storage Temperature	-65 ~ 150	°C

PW=5ms, Duty Cycle=10%

### $\textbf{Electrical Characteristics} \ \, \textbf{T}_{a} \!\!=\!\! 25^{\circ} \textbf{C} \ \, \textbf{unless otherwise noted}$

Symbol	Parameter	Test Condition	Min.	Тур.	Max.	Units
BV <sub>CEO</sub>	Collector-Emitter Breakdown Voltage	I <sub>C</sub> =10mA, I <sub>B</sub> =0				
	: BC635	_	45			V
	: BC637		60			V
	: BC639		80			V
I <sub>CBO</sub>	Collector Cut-off Current	$V_{CB}$ =30V, $I_E$ =0			0.1	μΑ
I <sub>EBO</sub>	Emitter Cut-off Current	$V_{EB}$ =5V, $I_C$ =0			0.1	μΑ
h <sub>FE1</sub>	DC Current Gain : All	V <sub>CE</sub> =2V, I <sub>C</sub> =5mA	25			
h <sub>FE2</sub>	: BC635	V <sub>CE</sub> =2V, I <sub>C</sub> =150mA	40		250	
	: BC637/BC639		40		160	
$h_{FE3}$	: All	$V_{CE}$ =2V, $I_{C}$ =500mA	25			
V <sub>CE</sub> (sat)	Collector-Emitter Saturation Voltage	I <sub>C</sub> =500mA, I <sub>B</sub> =50mA			0.5	V
V <sub>BE</sub> (on)	Base-Emitter On Voltage	$V_{CE}$ =2V, $I_{C}$ =500mA			1	V
f <sub>T</sub>	Current Gain Bandwidth Product	V <sub>CE</sub> =5V, I <sub>C</sub> =10mA, f=50MHz		100		MHz

## **Typical Characteristics**

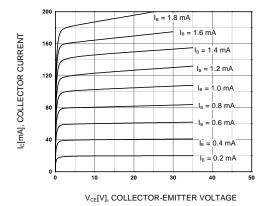


Figure 1. Static Characteristic

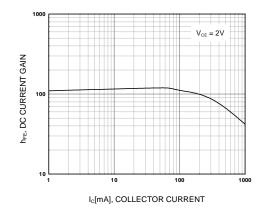


Figure 2. DC current Gain

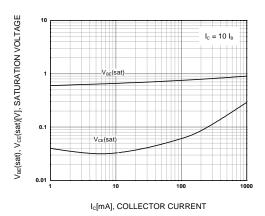


Figure 3. Base-Emitter Saturation Voltage Collector-Emitter Saturation Voltage

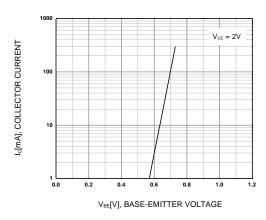


Figure 4. Base-Emitter On Voltage

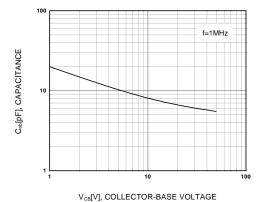
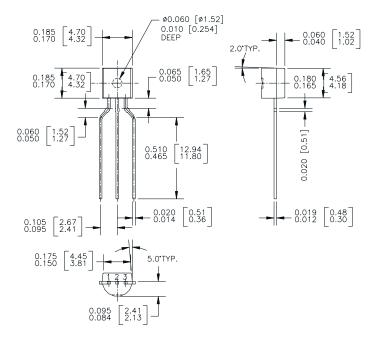


Figure 5. Collector Output Capacitance

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# **Package Dimensions**

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CoolFET™	FASTr™	MicroFET™	PowerTrench <sup>®</sup>	SuperSOT™-6
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E <sup>2</sup> CMOS™	HiSeC™	MSXPro™	Quiet Series™	TruTranslation™
EnSigna™	$I^2C^{TM}$	$OCX^{TM}$	RapidConfigure™	UHC™
Across the board.	. Around the world.™	OCXPro™	RapidConnect™	UltraFET <sup>®</sup>
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Programmable Active Droop™		OPTOPLANAR™	SMART START™	

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